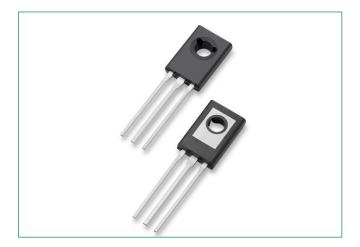
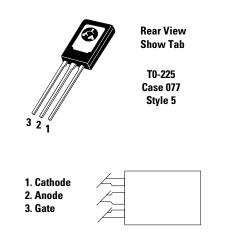


2N6071A/B Series



Pin Out



Description

Designed primarily for full-wave AC control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

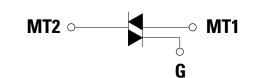
Features

- Sensitive Gate Triggering Uniquely Compatible for Direct Coupling to TTL, HTL, CMOS and Operational Amplifier Integrated Circuit Logic Functions
- Gate Triggering: 4 Mode -2N6071A, B; 2N6073A, B; 2N6075A, B
- Blocking Voltages to 600 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability

P0

- Small, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Lead-free package available

Functional Diagram



Additional Information







Samples

Maximum Ratings and Thermal Characteristics (T = 25°C unless otherwise noted)

Ŭ			
Rating	Symbol	Value	Unit
*Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open) 2N6071A,B 2N6073A,B 2N6075A,B	V _{drm} , V _{rrm}	200 400 600	-
*On-State RMS Current (T _c = 85°C) Full Cycle Sine Wave 50 to 60 Hz	I _{T(RMS)}	4.0	A
*Peak Non-repetitive Surge Current (One Full cycle, 60 Hz, $T_J = +110^{\circ}$ C)	I _{TSM}	30	A
Circuit Fusing Considerations (t = 8.3 ms)	l _{2t}	3.7	A2s
*Peak Gate Power (Pulse Width "1.0 $\mu s, T_c = 85^{\circ}C)$	P _{GM}	10	W
*Average Gate Power (t = 8.3 ms, $T_c = 85^{\circ}C$)	P _{G(AV)}	0.5	W
*Peak Gate Voltage (Pulse Width "1.0 μ s, T _c = 85°C)	V _{GM}	5.0	V
*Operating Junction Temperature Range	TJ	-40 to +110	°C
*Storage Temperature Range	T _{stg}	-40 to +150	°C
Mounting Torque (6-32 Screw) (Note 2)	_	8.0	in. lb.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

V_{DBM} and V_{BM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
Torque rating applies with use of a compression washer. Mounting torque in excess of 6 in. Ib. does not appreciably lower case-to-sink thermal resistance. Main terminal 2 and heatsink contact pad are common.

Thermal Characteristics

Rating	Symbol	Value	Unit
*Thermal Resistance, Junction to Case	R _{sJC}	3.5	°C/W
Thermal Resistance, Junction to Ambient (Note 1)	R _{BJA}	75	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	TL	260	C°

*Indicates JEDEC Registered Data

Electrical Characteristics · **OFF** ($T_c = 25^{\circ}$ C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
*Peak Repetitive Blocking CurrentTJ = 25°C (VD = VDRM = VRRM;	TJ = 25°C	IDRM,	-	-	10	μA
Gate Open)TJ = 110°C	TJ = 110°C	IRRM	-	-	2	mA

Electrical Characteristics - ON (TC = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Мах	Unit
*Peak On-State Voltage (Note 3) ($I_{TM} = \pm 6.0 \text{ A Peak}$)		С	-	-	2	V
*Gate Trigger Voltage (Continuous DC), All Quadrants (Main Terminal Voltage = 12 Vdc, $R_1 = 100 \Omega$, $T_1 = -40 °C$)		VGT	-	1.4	2.5	V
Gate Non-Trigger Voltage, All Quadrants (Main Terminal Voltage = 12 Vdc , RL = 100Ω , TJ = 110° C)		VGD	.02	-	-	V
*Holding Current	T ₁ = -40°C	IH	-	-	30	
(Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = ± 1 Adc)	T _J = -40°C T _J = 25°C	П	-	-	15	mA
Turn-On Time (I_{TM} = 14 Adc, I_{GT} = 100 mAdc)		tgt	-	1.5	-	μs
				QUAD (Maximu		

	Туре	IGT @ TJ	l mA	ll mA	III mA	IV mA
Gate Trigger Current (Continuous DC)	2N6071A 2N6073A	+25°C	5	5	5	10
(Main Terminal Voltage = 12 Vdc, RL = 100 Ω)	2N6073A 2N6075A	-40°C	20	20	20	30
	2N6071B	+25°C	3	3	3	5
	2N6073B 2N6075B	-40°C	15	15	15	20

3. Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

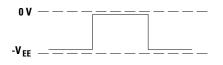
*Indicates JEDEC Registered Data.

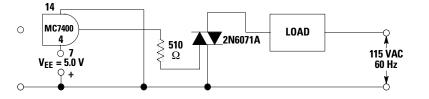


Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Commutation Voltage @ $V_{DRM'}T_J = 85^{\circ}C$, Gate Open, $I_{TM} = 5.7$ A, Exponential Waveform, Commutating di/dt = 2.0 A/ms	dv/dt(c)	-	5	10	V/µs

SAMPLE APPLICATION: TTL-Sensitive Gate 4 Ampere Triac Triggers in Modes II and III





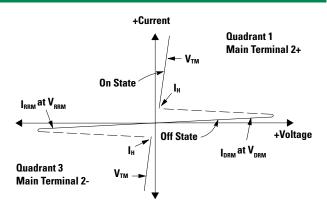
Trigger devices are recommended for gating on Triacs. They provide:

1. Consistent predictable turn-on points.

Simplified circuitry.
Fast turn-on time for cooler, more efficient and reliable operation.

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{drm}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current

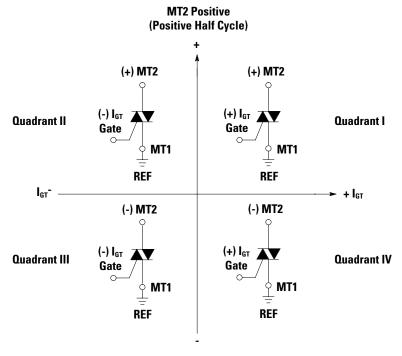


Sensitive Gate Logic Reference

IC Loris Functions	Firing Quadrant						
IC Logic Functions	I	Ш	III	IV			
TTL	_	2N6071A Series	2N6071A Series	_			
HTL	_	2N6071A Series	2N6071A Series	_			
CMOS (NAND)	2N6071B Series	_	_	2N6071B Series			
CMOS (Buffer)	-	2N6071B Series	2N6071B Series	_			
Operational Amplifier	2N6071A Series	_	_	2N6071A Series			
Zero Voltage Switch	_	2N6071A Series	2N6071A Series	_			



Quadrant Definitions for a Triac



MT2 Negative (Negative Half Cycle)



Thyristors Surface Mount – 200V-600W > 2N6071A/B Series

Ratings and Characteristic Curves

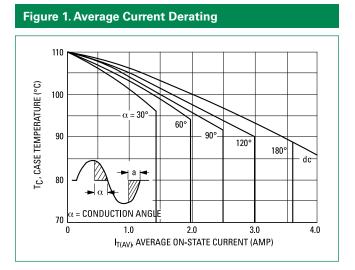


Figure 3. Power Dissipation

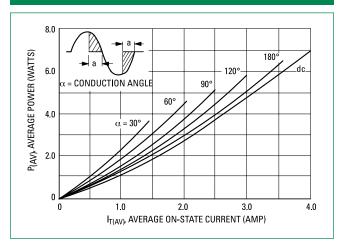


Figure 5. Typical Gate-Trigger Voltage

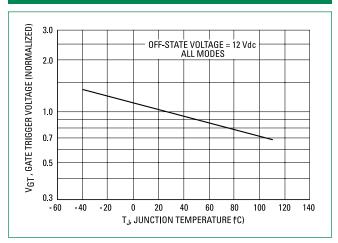


Figure 2. RMS Current Derating

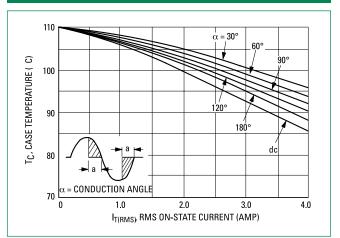


Figure 4. Power Dissipation

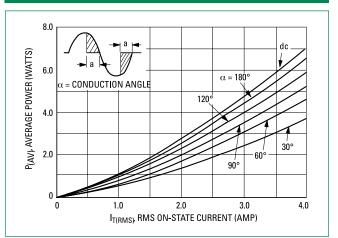


Figure 6. Typical Gate-Trigger Current

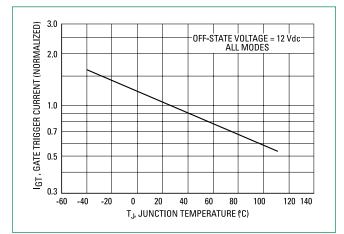




Figure 7. Maximum On-State Characteristics

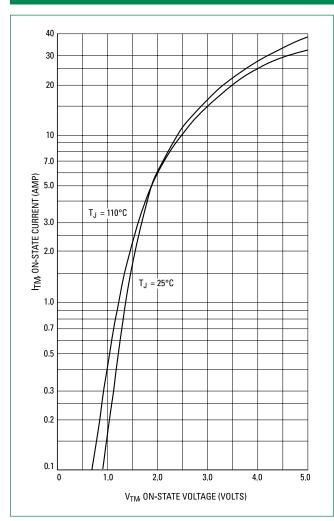


Figure 8. Typical Holding Current

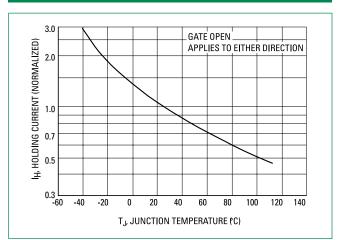


Figure 9. Maximum Allowable Surge Current

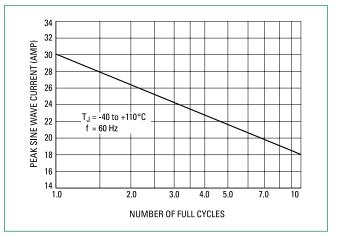
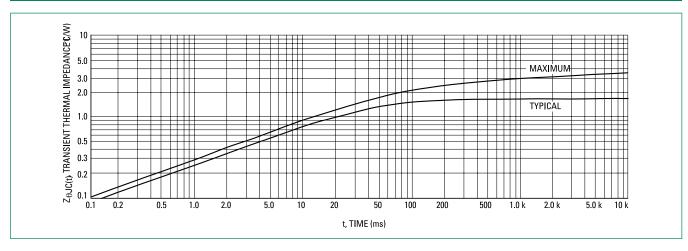


Figure 10. Thermal Response





Thyristors Surface Mount – 200V-600W > 2N6071A/B Series

Part Marking System

Rear View Show Tab

T0-225

Case 077

Style 5

1. Cathode

x =1,3,5

y =A,B Y =Year M =Month A =Assembly Site XX =Lot Serial Code

2. Anode

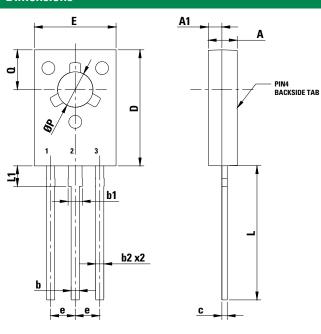
3. Gate

YMAXX

607xyG

2N





Inches Millimeters Dim Min Max Min Max 0.102 0.110 2.60 2.80 Α 0.047 0.055 1.20 1.40 A1 0.028 0.034 0.70 0.86 b 0.028 0.034 0.70 0.86 b2 С 0.019 0.022 0.49 0.57 D 0.417 0.449 10.60 11.40 Ε 0.291 0.323 7.40 8.20 0.090 TYP 2.29 TYP е L 0.551 0.630 14.00 16.00 2.70 L1 0.091 0.106 2.30 Ρ 3.40 0.118 0.134 3.00 Q 0.142 0.157 3.60 4.00 0.055 b1 0.047 1.2 1.4

Ordering Information Device Package Shipping[†] 2N6071A TO-225 2500 Units / Box TO-225 2N6071AG (Pb-Free) 2N6071AT TO-225 50 Units / Tube TO-225 2N6071ATG 1920 Units / Box (Pb-Free) 2N6071B TO-225 TO-225 2500 Units / Box 2N6071BG (Pb-Free) 2N6071BT TO-225 50 Units / Tube TO-225 1920 Units / Box 2N6071BTG (Pb-Free) 2N6073A TO-225 TO-225 2N6073AG (Pb-Free) 2N6073B TO-225 TO-225 2N6073BG (Pb-Free) 2500 Units / Box 2N6075A TO-225

TO-225

(Pb-Free)

TO-225

TO-225

(Pb-Free)

2N6075AG

2N6075B

2N6075BG

1. Dimensioning and Tolerancing Per ANSI Y14.5M, 1982.

Controlling Dimension: Inch.
077-01 Thru -08 Obsolete, New Standard 077-09.

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